

Abstract

An optoelectronic integrated circuit is fabricated by forming isolation trenches in a SOI structure to form at least first and second areas of silicon, by forming a first silicon island over the first silicon area during a first silicon forming step such that the first silicon island forms at least a portion of an optical device, by forming a second silicon island over the second silicon area during a second silicon forming step such that the first and second silicon forming steps are separate silicon forming steps, and by processing at least the second silicon area to form an electronic device with the second silicon island.